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Band structures and optical properties modulation of holey C$_2$N nanosheets by alloying with group IV and V elements

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Fig. S1 The real part $\varepsilon_1(\omega)$, imaginary part $\varepsilon_2(\omega)$ of the dielectric function and the optical absorption coefficients as a function of photon energy along the x-y plane of the 2D C$_2$N unitcell using the (a)MGGA and (b)HSE06 methods, respectively.